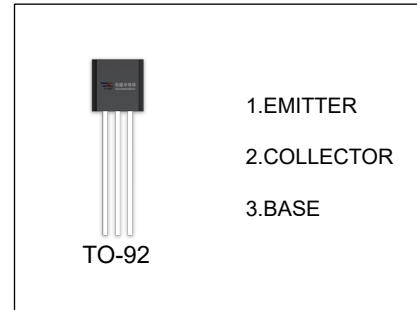


3DD13002S TRANSISTOR (NPN)

FEATURES

- Power switching applications



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
3DD13002S	TO-92	Bulk	1000pcs/Bag
3DD13002S-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	600	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	1	A
P_C	Collector Power Dissipation	0.75	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	167	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	600			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=600\text{V}, I_E=0$			100	μA
Collector cut-off current	I_{CEO}	$V_{CE}=400\text{V}, I_B=0$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}, I_C=200\text{mA}$	9		40	
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C=250\mu\text{A}$	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=200\text{mA}, I_B=40\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=200\text{mA}, I_B=40\text{mA}$			1.1	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=1\text{MHz}$	5			MHz
Fall time	t_f	$I_C=1\text{A}, I_{B1}=I_{B2}=0.2\text{A}, V_{CC}=100\text{V}$			0.5	μs
Storage time	t_S	$I_C=1\text{A}, I_{B1}=I_{B2}=0.2\text{A}, V_{CC}=100\text{V}$			2.5	μs

CLASSIFICATION of $h_{FE(1)}$

Range	9-15	15-20	20-25	25-30	30-35	35-40

CLASSIFICATION of $V_{CE(sat)}$

Rank	A	B
Range	<0.25	0.25-0.45